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What is "[Embedded - Microcontrollers](#)"?

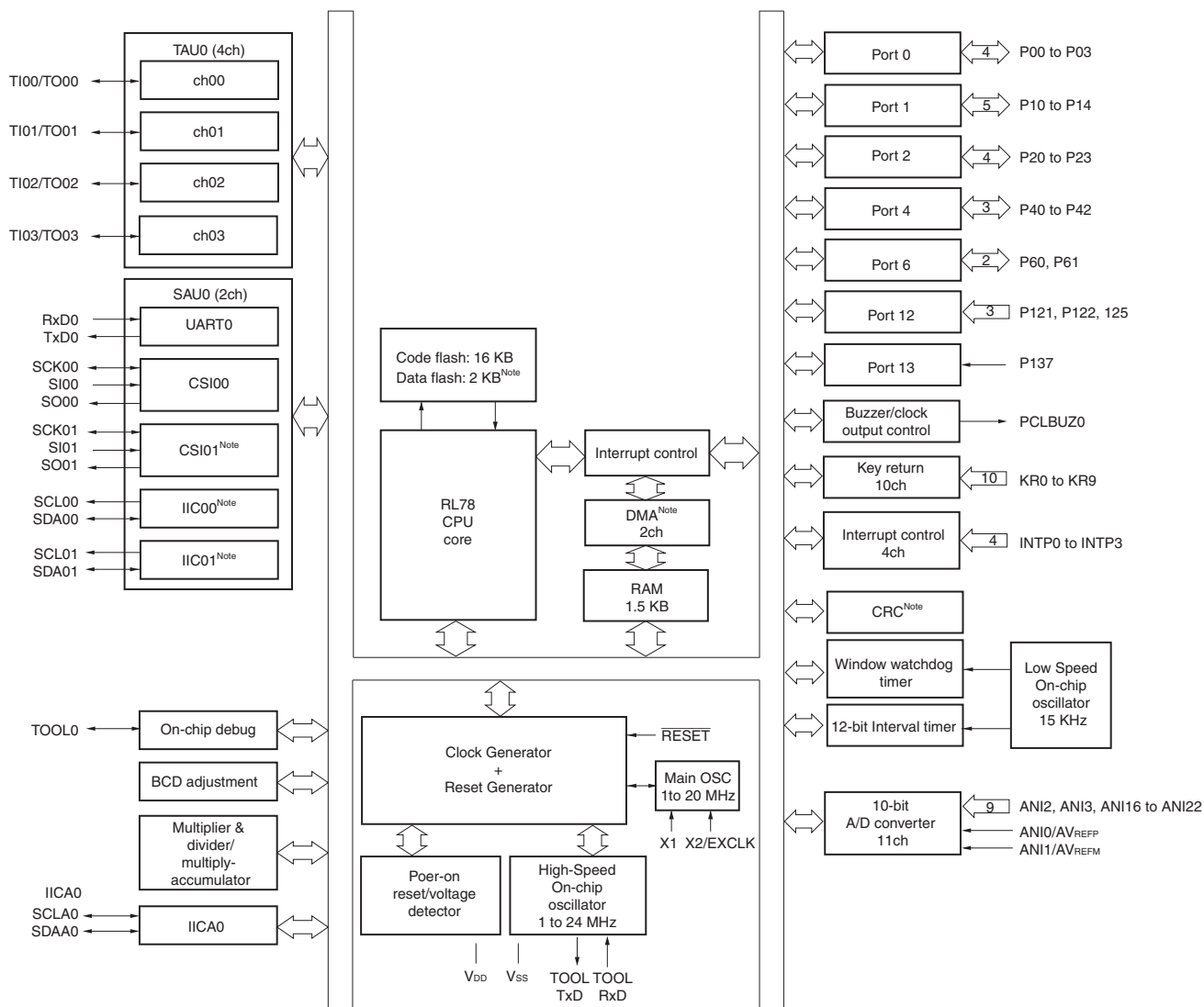
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	18
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10378ana-u0

1.6.2 24-pin products



Note Provided only in the R5F102 products.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	I _{OH1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			–10.0 ^{Note 2}	mA
		20-, 24-pin products: Total of P40 to P42	4.0 V ≤ V _{DD} ≤ 5.5 V		–30.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		–6.0	mA
		30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V		–4.5	mA
		20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14	4.0 V ≤ V _{DD} ≤ 5.5 V		–80.0	mA
			2.7 V ≤ V _{DD} < 4.0 V		–18.0	mA
		30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V		–10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})			–100	mA
	I _{OH2}	Per pin for P20 to P23			–0.1	mA
		Total of all pins			–0.4	mA

Notes 1. value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = –10.0 mA

$$\text{Total output current of pins} = (-10.0 \times 0.7) / (80 \times 0.01) \cong -8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

($T_A = -40$ to $+85^\circ\text{C}$, $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**(3/4)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$0.8V_{DD}$		V_{DD}	V
	V_{IH2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.2	V_{DD}	V
			$3.3\text{ V} \leq V_{DD} < 4.0\text{ V}$	2.0	V_{DD}	V
			$1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$	1.5	V_{DD}	V
	V_{IH3}	P20 to P23	$0.7V_{DD}$		V_{DD}	V
	V_{IH4}	P60, P61	$0.7V_{DD}$		6.0	V
Input voltage, low	V_{IH5}	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET	$0.8V_{DD}$		V_{DD}	V
	V_{IL1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	0		$0.2V_{DD}$	V
	V_{IL2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	0	0.8	V
			$3.3\text{ V} \leq V_{DD} < 4.0\text{ V}$	0	0.5	V
			$1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$	0	0.32	V
Output voltage, high	V_{IL3}	P20 to P23	0		$0.3V_{DD}$	V
	V_{IL4}	P60, P61	0		$0.3V_{DD}$	V
	V_{IL5}	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET	0		$0.2V_{DD}$	V
	V_{OH1}	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OH1} = -10.0\text{ mA}$	$V_{DD}-1.5$		V
			$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OH1} = -3.0\text{ mA}$	$V_{DD}-0.7$		V
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OH1} = -2.0\text{ mA}$	$V_{DD}-0.6$		V
			$1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $I_{OH1} = -1.5\text{ mA}$	$V_{DD}-0.5$		V
Output voltage, low	V_{OH2}	P20 to P23	$I_{OH2} = -100\text{ }\mu\text{A}$	$V_{DD}-0.5$		V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(3) Peripheral functions (Common to all products)**(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	I _{FIL} ^{Note 1}				0.20		μA
12-bit interval timer operating current	I _{TMKA} ^{Notes 1, 2, 3}				0.02		μA
Watchdog timer operating current	I _{WDT} ^{Notes 1, 2, 4}	f _{IL} = 15 kHz			0.22		μA
A/D converter operating current	I _{ADC} ^{Notes 1, 5}	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.30	1.70	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	I _{ADREF} ^{Note 1}				75.0		μA
Temperature sensor operating current	I _{TMPS} ^{Note 1}				75.0		μA
LVD operating current	I _{LVD} ^{Notes 1, 6}				0.08		μA
Self-programming operating current	I _{FSP} ^{Notes 1, 8}				2.00	12.20	mA
BGO operating current	I _{BGO} ^{Notes 1, 7}				2.00	12.20	mA
SNOOZE operating current	I _{SNOZ} ^{Note 1}	ADC operation	The mode is performed ^{Note 9}		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to the V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3}, and I_{FIL} and I_{TMKA} when the 12-bit interval timer operates.4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.

7. Current flowing only during data flash rewrite.

8. Current flowing only during self programming.

9. For shift time to the SNOOZE mode, see **17.3.3 SNOOZE mode**.**Remarks** 1. f_{IL}: Low-speed on-chip oscillator clock frequency2. Temperature condition of the TYP. value is T_A = 25°C

- Notes**
1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1
 2. When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (V_{DD} tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).
For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

- Remarks**
1. R_b [Ω]: Communication line (SCK00, SO00) pull-up resistance, C_b [F]: Communication line (SCK00, SO00) load capacitance, V_b [V]: Communication line voltage
 2. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AV_{REFM} (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

($T_A = -40$ to $+85^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = V_{BGR} ^{Note 3}, Reference voltage (–) = AV_{REFM}
^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	t_{CONV}	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			± 2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			± 1.0	LSB
Analog input voltage	V_{AIN}		0		V_{BGR} ^{Note 3}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **28.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS} , the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM} .

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

2.6.2 Temperature sensor/internal reference voltage characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, HS (high-speed main) mode)

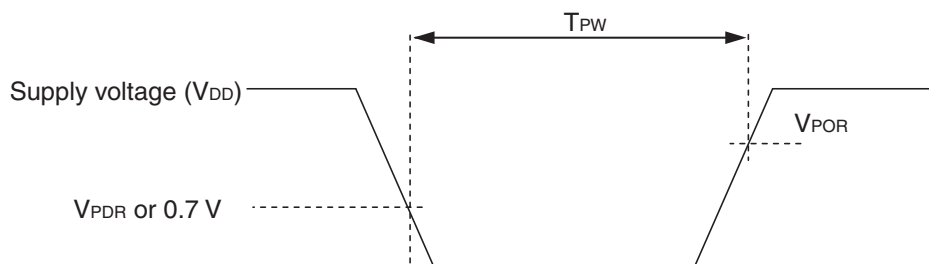
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	t_{AMP}		5			μs

2.6.3 POR circuit characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR} . This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



LVD detection voltage of interrupt & reset mode**($T_A = -40$ to $+85^\circ\text{C}$, $V_{PDR} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V _{LVD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	V _{LVD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	V _{LVD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	V _{LVD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	V _{LVD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	V _{LVD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	V _{LVD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	V _{LVD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	V _{LVD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	V _{LVD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	V _{LVD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics**($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S _{VDD}				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 28.4 AC Characteristics.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}\text{C}$)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V_{DD}			-0.5 to $+6.5$	V
REGC terminal input voltage ^{Note 1}	V_{IREGC}	REGC		-0.3 to $+2.8$ and -0.3 to $V_{DD} + 0.3$ ^{Note 2}	V
Input Voltage	V_{I1}	Other than P60, P61		-0.3 to $V_{DD} + 0.3$ ^{Note 3}	V
	V_{I2}	P60, P61 (N-ch open drain)		-0.3 to 6.5	V
Output Voltage	V_O			-0.3 to $V_{DD} + 0.3$ ^{Note 3}	V
Analog input voltage	V_{AI}	20, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		-0.3 to $V_{DD} + 0.3$ and -0.3 to $AVREF(+)+0.3$ ^{Notes 3, 4}	V
Output current, high	I_{OH1}	Per pin	Other than P20 to P23	-40	mA
		Total of all pins	All the terminals other than P20 to P23	-170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	-70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	-100	mA
	I_{OH2}	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low	I_{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I_{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A			-40 to $+105$	$^{\circ}\text{C}$
Storage temperature	T_{stg}			-65 to $+150$	$^{\circ}\text{C}$

Notes 1. 30-pin product only.

2. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.

3. Must be 6.5 V or lower.

4. Do not exceed $AVREF(+) + 0.3$ V in case of A/D conversion target pin.

5. 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AVREF(+)$: + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

(2) 30-pin products

 $(T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V})$

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current <small>Note 1</small>	I _{DD2} <small>Note 2</small>	HALT mode	HS (High-speed main) mode <small>Note 6</small>	f _{IH} = 24 MHz <small>Note 4</small>	V _{DD} = 5.0 V		440	2300	μA
					V _{DD} = 3.0 V		440	2300	
				f _{IH} = 16 MHz <small>Note 4</small>	V _{DD} = 5.0 V		400	1700	μA
					V _{DD} = 3.0 V		400	1700	
				f _{MX} = 20 MHz <small>Note 3</small> , V _{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 20 MHz <small>Note 3</small> , V _{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 10 MHz <small>Note 3</small> , V _{DD} = 5.0 V	Square wave input		190	1020	μA
					Resonator connection		260	1100	
				f _{MX} = 10 MHz <small>Note 3</small> , V _{DD} = 3.0 V	Square wave input		190	1020	μA
					Resonator connection		260	1100	
	I _{DD3} <small>Note 5</small>	STOP mode	T _A = −40°C				0.18	0.50	μA
			T _A = +25°C				0.23	0.50	
			T _A = +50°C				0.30	1.10	
			T _A = +70°C				0.46	1.90	
			T _A = +85°C				0.75	3.30	
			T _A = +105°C				2.94	15.30	

Notes 1. Total current flowing into V_{DD} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: $V_{DD} = 2.7\text{ V}$ to 5.5 V @ 1 MHz to 24 MHz

$V_{DD} = 2.4\text{ V}$ to 5.5 V @ 1 MHz to 16 MHz

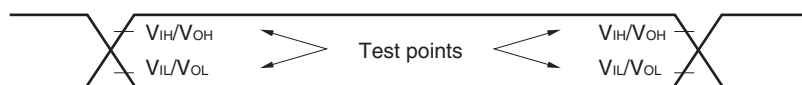
Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH} : high-speed on-chip oscillator clock frequency

3. Except STOP mode, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$.

3.5 Peripheral Functions Characteristics

AC Timing Test Point



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

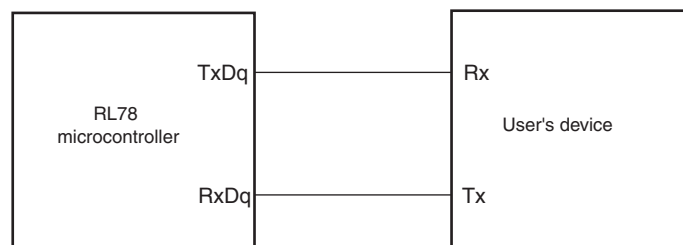
($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate <small>Note 1</small>		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK}$ <small>Note2</small>		$f_{MCK}/12$	bps
				2.0	Mbps

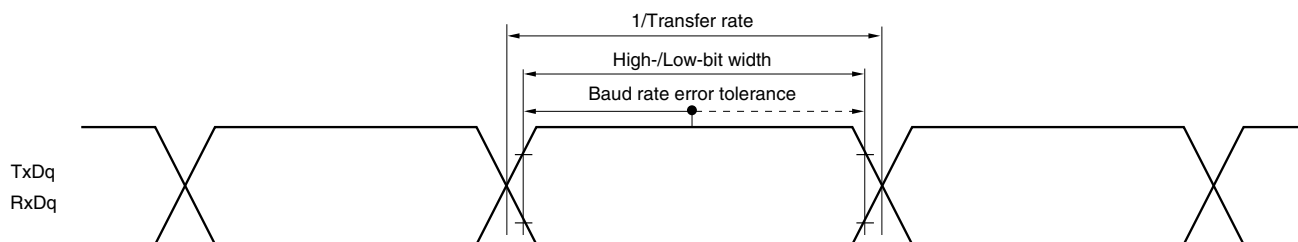
- Notes**
- Transfer rate in the SNOOZE mode is 4800 bps only.
 - The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
 HS (high-speed main) mode: 24 MHz ($2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$)
 16 MHz ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- Remarks**
- q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)
 - f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

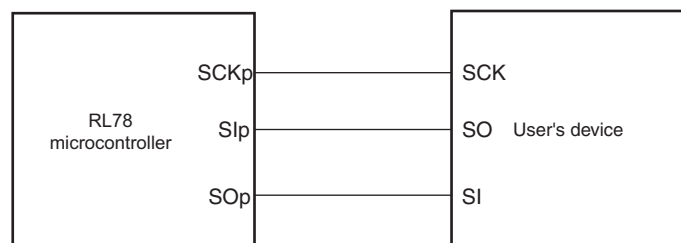
(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)
($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 4}	t_{KCY2}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	$20\text{ MHz} < f_{MCK}$	$16/f_{MCK}$		ns
			$f_{MCK} \leq 20\text{ MHz}$	$12/f_{MCK}$		ns
		$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	$16\text{ MHz} < f_{MCK}$	$16/f_{MCK}$		ns
			$f_{MCK} \leq 16\text{ MHz}$	$12/f_{MCK}$		ns
		$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$12/f_{MCK}$ and 1000		ns
SCKp high-/low-level width	t_{KH2} , t_{KL2}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$t_{KCY2}/2-14$		ns
		$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$t_{KCY2}/2-16$		ns
		$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$t_{KCY2}/2-36$		ns
Slp setup time (to SCKp \uparrow) ^{Note 1}	t_{SIK2}	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$1/f_{MCK} + 40$		ns
		$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$1/f_{MCK} + 60$		ns
Slp hold time (from SCKp \uparrow) ^{Note 2}	t_{KSI2}			$1/f_{MCK} + 62$		ns
Delay time from SCKp \downarrow to SOp output ^{Note 3}	t_{KSO2}	$C = 30\text{ pF}$ ^{Note 4}	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$2/f_{MCK} + 66$	ns
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		$2/f_{MCK} + 113$	ns

- Notes**
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp \downarrow ” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp \downarrow ” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp \uparrow ” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. C is the load capacitance of the SOp output lines.
 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

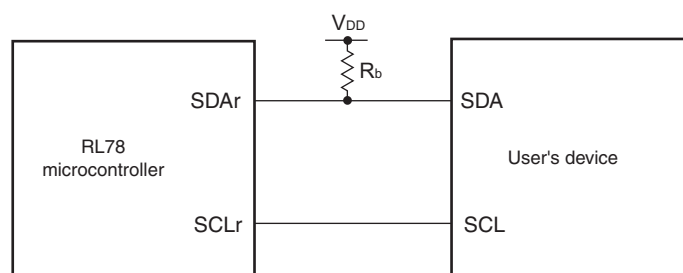
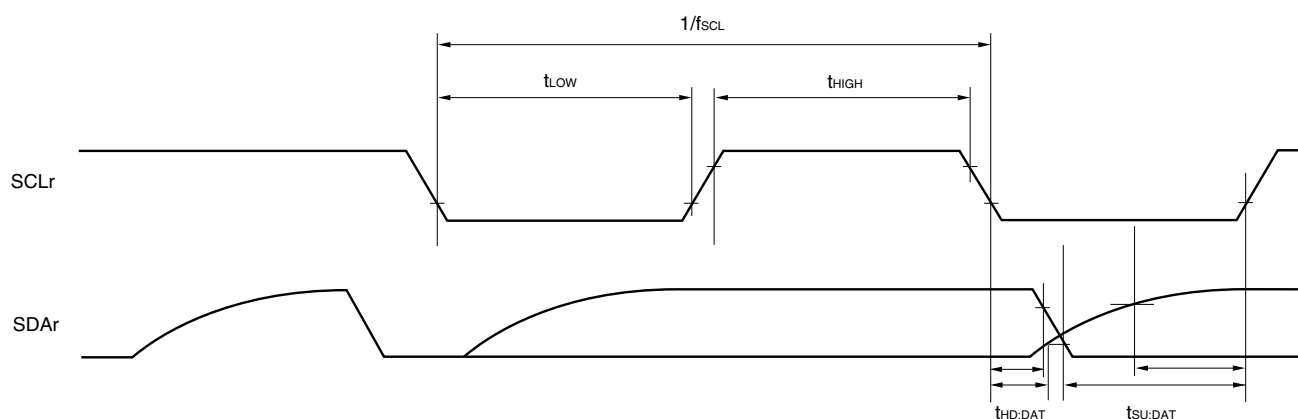
Caution Select the normal input buffer for the Slp and SCKp pins and the normal output mode for the SOp pin by selecting port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

CSI mode connection diagram (during communication at same potential)



(4) During communication at same potential (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t_{LOW}	$C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	$C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Data setup time (reception)	$t_{\text{SU:DAT}}$	$C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	$1/f_{\text{MCK}} + 580$ ^{Note 2}		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	0	1420	ns

Notes 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.**2.** Set $t_{\text{SU:DAT}}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".**Caution** Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).**Simplified I²C mode connection diagram (during communication at same potential)****Simplified I²C mode serial transfer timing (during communication at same potential)****Remarks 1.** R_b [Ω]: Communication line (SDAr) pull-up resistance C_b [F]: Communication line (SCLr, SDAr) load capacitance**2.** r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)**3.** f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))

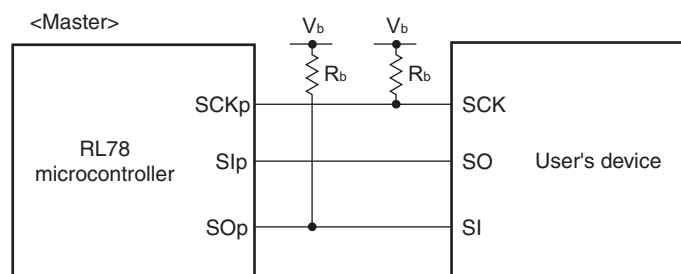
(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

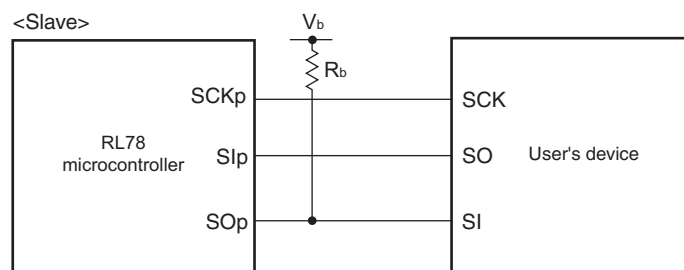
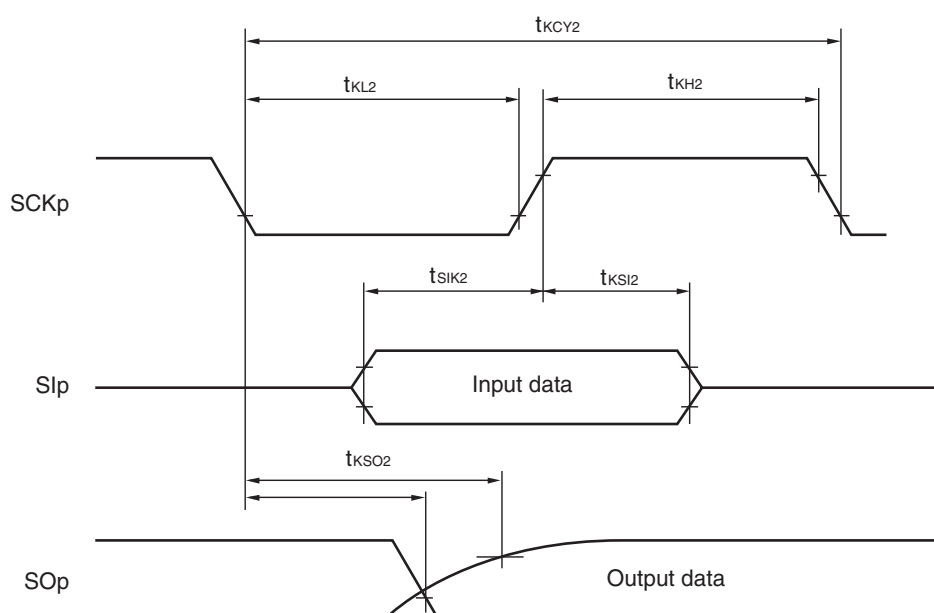
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp↓) <small>Note</small>	t_{SIK1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	88		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	88		ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	220		ns
Slp hold time (from SCKp↓) <small>Note</small>	t_{KSI1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$	38		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	38		ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	38		ns
Delay time from SCKp↑ to SO _p output <small>Note</small>	t_{KSO1}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$		50	ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		50	ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$		50	ns

Note When $DAP_{mn} = 0$ and $CKP_{mn} = 1$, or $DAP_{mn} = 1$ and $CKP_{mn} = 0$.

- Cautions 1.** Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SO_p pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.
- 2.** CSI01 and CSI11 cannot communicate at different potential.

- Remarks 1.** R_b [Ω]: Communication line (SCKp, SO_p) pull-up resistance, C_b [F]: Communication line (SCKp, SO_p) load capacitance, V_b [V]: Communication line voltage
- 2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

CSI mode connection diagram (during communication at different potential)

CSI mode connection diagram (during communication at different potential)
CSI mode serial transfer timing (slave mode) (during communication at different potential)
 (When $DAPmn = 0$ and $CKPmn = 0$, or $DAPmn = 1$ and $CKPmn = 1$.)


- Remarks**
1. R_b [Ω]: Communication line (SOp) pull-up resistance, C_b [F]: Communication line (SOp) load capacitance, V_b [V]: Communication line voltage
 2. p : CSI number ($p = 00, 20$), m : Unit number ($m = 0, 1$), n : Channel number ($n = 0$)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m ($SPSm$) and the $CKSmn$ bit of serial mode register mn ($SMRmn$))

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$		100^{Note1}	kHz
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		100^{Note1}	kHz
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$		100^{Note1}	kHz
Hold time when SCLr = "L"	t_{LOW}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	4600		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	4600		ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	4650		ns
Hold time when SCLr = "H"	t_{HIGH}	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	2700		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	2400		ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	1830		ns
Data setup time (reception)	$t_{SU:DAT}$	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	$1/f_{MCK}$ + 760 ^{Note3}		ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{MCK}$ + 760 ^{Note3}		ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$1/f_{MCK}$ + 570 ^{Note3}		ns
Data hold time (transmission)	$t_{HD:DAT}$	$4.0\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	0	1420	ns
		$2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	1420	ns
		$2.4\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	0	1215	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.2. Set $t_{SU:DAT}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

2. IIC01 and IIC11 cannot communicate at different potential.

(Remarks are listed on the next page.)

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-) = AV_{REFM}
ANI0 to ANI3	Refer to 29.6.1 (1).	Refer to 29.6.1 (3).	Refer to 29.6.1 (4).
ANI16 to ANI22	Refer to 29.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 29.6.1 (1).		—

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}		1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.25	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3	0		AV_{REFP}	V
		Internal reference voltage (HS (high-speed main) mode)	V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (HS (high-speed main) mode)	V_{TMPS25} ^{Note 4}			V

(Notes are listed on the next page.)

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. Refer to **29.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI16 to ANI22

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}		1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI22	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.35	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI22	0		AV_{REFP} and V_{DD}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

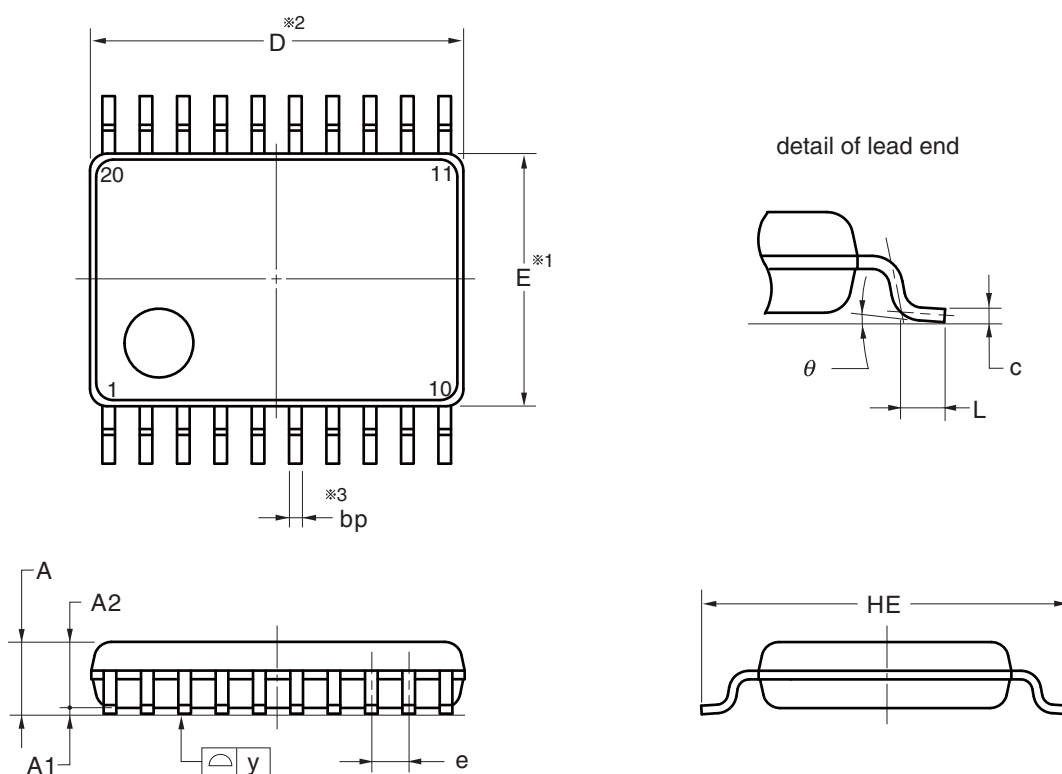
4. PACKAGE DRAWINGS

4.1 20-pin products

R5F1026AASP, R5F10269ASP, R5F10268ASP, R5F10267ASP, R5F10266ASP
 R5F1036AASP, R5F10369ASP, R5F10368ASP, R5F10367ASP, R5F10366ASP
 R5F1026ADSP, R5F10269DSP, R5F10268DSP, R5F10267DSP, R5F10266DSP
 R5F1036ADSP, R5F10369DSP, R5F10368DSP, R5F10367DSP, R5F10366DSP
 R5F1026AGSP, R5F10269GSP, R5F10268GSP, R5F10267GSP, R5F10266GSP

<R>

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



NOTE

1. Dimensions "※1" and "※2" do not include mold flash.
2. Dimension "※3" does not include trim offset.

(UNIT:mm)

ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
A	1.45 MAX.
A1	0.10±0.10
A2	1.15
e	0.65±0.12
bp	0.22 ^{+0.10} _{-0.05}
c	0.15 ^{+0.05} _{-0.02}
L	0.50±0.20
y	0.10
θ	0° to 10°

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